

SNx4HC132 Quadruple 2-Input NAND Gates with Schmitt-Trigger Inputs

1 Features

- Buffered inputs
- Wide operating temperature range:
–40°C to +85°C
- Supports fanout up to 10 LSTTL loads
- Significant power reduction compared to LSTTL logic ICs

2 Applications

- [Alarm / tamper detect circuit](#)
- S-R latch

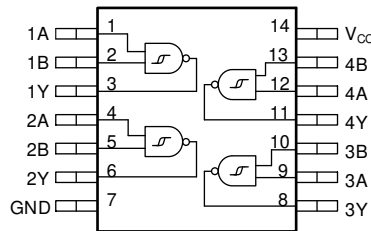
3 Description

This device contains four independent 2-input NAND gates. Each gate performs the Boolean function $Y = \overline{A \bullet B}$ in positive logic.

Device Information

PART NUMBER	PACKAGE ⁽¹⁾	BODY SIZE (NOM)
SN74HC132D	SOIC (14)	8.65 mm × 3.90 mm
SN74HC132DB	SSOP (14)	6.20 mm × 5.30 mm
SN74HC132N	PDIP (14)	19.30 mm × 6.40 mm
SN74HC132NS	SO (14)	10.20 mm × 5.30 mm
SN74HC132PW	TSSOP (14)	5.00 mm × 4.40 mm
SN54HC132J	CDIP (14)	19.94 mm × 7.62 mm
SN54HC132W	CDIP (14)	9.20 mm × 6.29 mm
SN54HC132FK	LCCC (20)	8.89 mm × 8.89 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.



Device functional pinout



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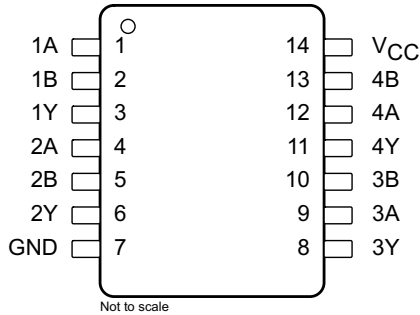
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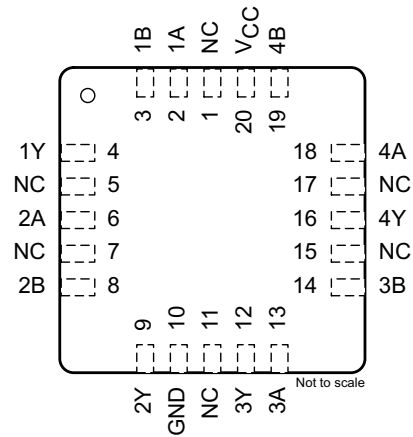
Changes from Revision G (January 2016) to Revision H (January 2021)	Page
• Updated data sheet to new template.....	1
• Thermal values changed for all packages.....	4

Changes from Revision F (November 2004) to Revision G (January 2016)	Page
• Added <i>ESD Ratings</i> table, <i>Feature Description</i> section, <i>Device Functional Modes</i> , <i>Application and Implementation</i> section, <i>Power Supply Recommendations</i> section, <i>Layout</i> section, <i>Device and Documentation Support</i> section, and <i>Mechanical, Packaging, and Orderable Information</i> section.....	1
• Removed Ordering Information table, see POA at the end of the data sheet.....	1

5 Pin Configuration and Functions



**Figure 5-1. D, DB, N, NS, J, W, or PW Package
14-Pin SOIC, SSOP, PDIP, SO, or TSSOP
Top View**



**Figure 5-2. FK Package
20-Pin LCCC
Top View**

Pin Functions ⁽¹⁾

NAME	PIN		I/O	DESCRIPTION
	SOIC, SSOP, PDIP, SO, TSSOP	LCCC		
1A	1	2	I	1A Input
1B	2	3	I	1B Input
1Y	3	4	O	1Y Output
2A	4	6	I	2A Input
2B	5	8	I	2B Input
2Y	6	9	O	2Y Output
3A	9	13	I	3A Input
3B	10	14	I	3B Input
3Y	8	12	O	3Y Output
4A	12	18	I	4A Input
4B	13	19	I	4B Input
4Y	11	16	O	4Y Output
GND	7	10	—	Ground Pin
NC	—	1, 5, 7, 11, 15, 17	—	No Connection
V _{CC}	14	20	—	Power Pin

(1) NC – no connection

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{CC}	Supply voltage	-0.5	7	V
I _{IK}	Input clamp current ⁽²⁾	V _I < -0.5 V or V _I > V _{CC}		±20 mA
I _{OK}	Output clamp current ⁽²⁾	V _O < -0.5 V or V _O > V _{CC}		±20 mA
I _O	Continuous output current	V _O = 0 to V _{CC}		±25 mA
	Continuous current through V _{CC} or GND			±50 mA
T _J	Junction temperature ⁽³⁾			150 °C
T _{stg}	Storage temperature	-65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Rating* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Condition*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) Guaranteed by design.

6.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V _{CC}	Supply voltage	2	5	6	V
V _I	Input voltage	0		V _{CC}	V
V _O	Output voltage	0		V _{CC}	V
T _A	Ambient temperature	SN54HC132		125	°C
		SN74HC132	-40	85	

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		SN74HC132					UNIT
		D (SOIC)	DB (SSOP)	N (PDIP)	NS (SO)	PW (TSSOP)	
		14 PINS	14 PINS	14 PINS	14 PINS	14 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	133.6	106.8	61.5	122.6	151.7	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	89	56.4	49.3	81.8	79.4	°C/W
R _{θJB}	Junction-to-board thermal resistance	89.5	57.0	41.3	83.8	94.7	°C/W
ψ _{JT}	Junction-to-top characterization parameter	45.5	16.9	28.9	45.4	25.2	°C/W
ψ _{JB}	Junction-to-board characterization parameter	89.1	56.3	41.1	83.4	94.1	°C/W

THERMAL METRIC ⁽¹⁾		SN74HC132					UNIT
		D (SOIC)	DB (SSOP)	N (PDIP)	NS (SO)	PW (TSSOP)	
		14 PINS	14 PINS	14 PINS	14 PINS	14 PINS	
$R_{\theta_{JC(bot)}}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.5 Electrical Characteristics - Commercial (74xx)

over operating free-air temperature range; typical values measured at $T_A = 25^\circ\text{C}$ (unless otherwise noted).

PARAMETER		TEST CONDITIONS		V_{CC}	Operating free-air temperature (T_A)						UNIT
					25°C			-40°C to 85°C			
					MIN	TYP	MAX	MIN	TYP	MAX	
V_{T+}	Positive switching threshold			2 V	0.7	1.2	1.5	0.7	1.5	V	
				4.5 V	1.55	.5	3.15	1.55	3.15		
				6 V	2.1	3.3	4.2	2.1	4.2		
V_{T-}	Negative switching threshold			2 V	0.3	0.6	1.0	0.3	1.0	V	
				4.5 V	0.9	1.6	2.45	0.9	2.45		
				6 V	1.2	2.0	3.2	1.2	3.2		
ΔV_T	Hysteresis ($V_{T+} - V_{T-}$)			2 V	0.2	0.6	1.2	0.2	1.2	V	
				4.5 V	0.4	0.9	2.1	0.4	2.1		
				6 V	0.5	1.3	2.5	0.5	2.5		
V_{OH}	High-level output voltage	$V_I = V_{IH}$ or V_{IL}	$I_{OH} = -20 \mu\text{A}$	2 V	1.9	1.998		1.9		V	
				4.5 V	4.4	4.499		4.4			
				6 V	5.9	5.999		5.9			
			$I_{OH} = -4 \text{ mA}$	4.5 V	3.98	4.3			3.84		
			$I_{OH} = -5.2 \text{ mA}$	6 V	5.48	5.8		5.34			
V_{OL}	Low-level output voltage	$V_I = V_{IH}$ or V_{IL}	$I_{OL} = 20 \mu\text{A}$	2 V		0.002	0.1		0.1	V	
				4.5 V		0.001	0.1		0.1		
				6 V		0.001	0.1		0.1		
			$I_{OL} = 4 \text{ mA}$	4.5 V		0.17	0.26		0.33		
			$I_{OL} = 5.2 \text{ mA}$	6 V		0.15	0.26		0.33		
I_I	Input leakage current	$V_I = V_{CC}$ or 0		6 V		± 0.1	± 100		± 1000	nA	
I_{CC}	Supply current	$V_I = V_{CC}$ or 0	$V_I = V_{CC}$ or 0	6 V			2		20	μA	
C_i	Input capacitance			2 V to 6 V		3	10		10	pF	
C_{pd}	Power dissipation capacitance per gate	No load		2 V to 6 V		20				pF	

6.6 Electrical Characteristics - Military (54xx)

over operating free-air temperature range; typical values measured at $T_A = 25^\circ\text{C}$ (unless otherwise noted).

PARAMETER		TEST CONDITIONS		V_{CC}	Operating free-air temperature (T_A)						UNIT
					25°C			-55°C to 125°C			
					MIN	TYP	MAX	MIN	TYP	MAX	
V_{T+}	Positive switching threshold			2 V	0.7	1.2	1.5	0.7	1.5	V	
				4.5 V	1.55	.5	3.15	1.55	3.15		
				6 V	2.1	3.3	4.2	2.1	4.2		
V_{T-}	Negative switching threshold			2 V	0.3	0.6	1.0	0.3	1.0	V	
				4.5 V	0.9	1.6	2.45	0.9	2.45		
				6 V	1.2	2.0	3.2	1.2	3.2		
ΔV_T	Hysteresis ($V_{T+} - V_{T-}$)			2 V	0.2	0.6	1.2	0.2	1.2	V	
				4.5 V	0.4	0.9	2.1	0.4	2.1		
				6 V	0.5	1.3	2.5	0.5	2.5		
V_{OH}	High-level output voltage	$V_I = V_{IH}$ or V_{IL}	$I_{OH} = -20 \mu\text{A}$	2 V	1.9	1.998		1.9		V	
				4.5 V	4.4	4.499		4.4			
				6 V	5.9	5.999		5.9			
			$I_{OH} = -4 \text{ mA}$	4.5 V	3.98	4.3		3.7			
				6 V	5.48	5.8		5.2			
V_{OL}	High-level output voltage	$V_I = V_{IH}$ or V_{IL}	$I_{OL} = 20 \mu\text{A}$	2 V			0.002	0.1		V	
				4.5 V			0.001	0.1			
				6 V			0.001	0.1			
			$I_{OL} = 4 \text{ mA}$	4.5 V			0.17	0.26			0.4
				6 V			0.15	0.26			0.4
I_I	Input leakage current	$V_I = V_{CC}$ or 0		6 V			± 0.1	± 100		± 1000	nA
I_{CC}	Supply current	$V_I = V_{CC}$ or 0	$V_I = V_{CC}$ or 0	6 V				2		40	μA
C_i	Input capacitance			2 V to 6 V			3	10		10	pF
C_{pd}	Power dissipation capacitance per gate	No load		2 V to 6 V			20				pF

6.7 Switching Characteristics - Commercial (74xx)

over operating free-air temperature range (unless otherwise noted)

PARAMETER		FROM	TO	V_{CC}	Operating free-air temperature (T_A)						UNIT
					25°C			-40°C to 85°C			
					MIN	TYP	MAX	MIN	TYP	MAX	
t_{pd}	Propagation delay	A or B	Y	2 V		60				156	ns
				4.5 V		18			31		
				6 V		14			27		
t_t	Transition-time		Any	2 V		28				95	ns
				4.5 V		8			19		
				6 V		6			16		

6.8 Switching Characteristics - Military (54xx)

over operating free-air temperature range (unless otherwise noted)

PARAMETER	FROM	TO	V _{CC}	Operating free-air temperature (T _A)						UNIT	
				25°C			-55°C to 125°C				
				MIN	TYP	MAX	MIN	TYP	MAX		
t _{pd}	Propagation delay	A or B	Y	2 V	60			186			ns
				4.5 V	18			37			
				6 V	14			32			
t _t	Transition-time		Any	2 V	28			110			ns
				4.5 V	8			22			
				6 V	6			19			

6.9 Typical Characteristics

T_A = 25°C

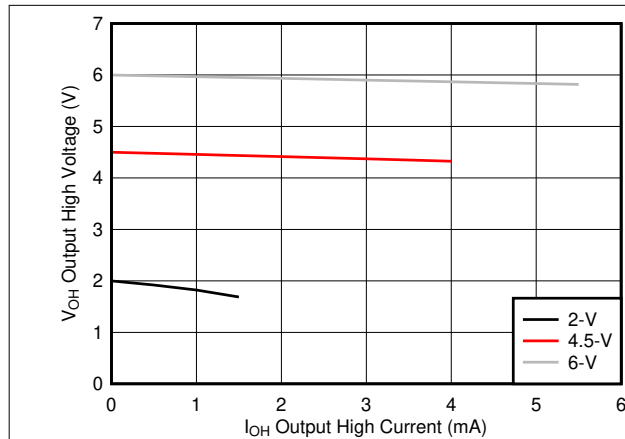


Figure 6-1. Typical output voltage in the high state (V_{OH})

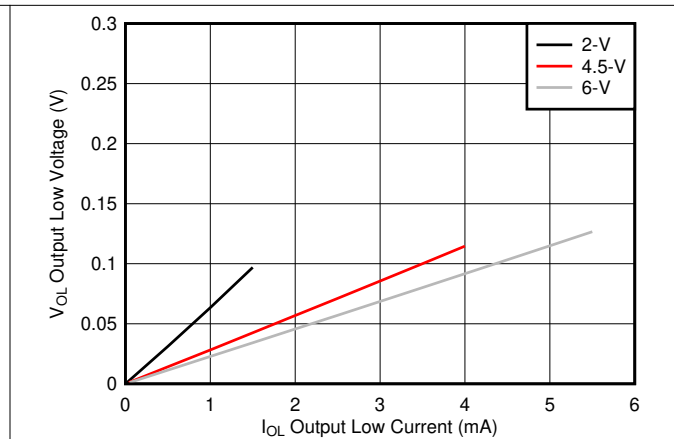


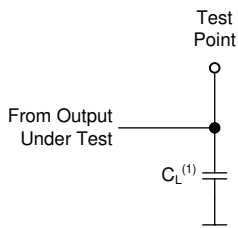
Figure 6-2. Typical output voltage in the low state (V_{OL})

7 Parameter Measurement Information

Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: $PRR \leq 1 \text{ MHz}$, $Z_O = 50 \ \Omega$, $t_t < 6 \text{ ns}$.

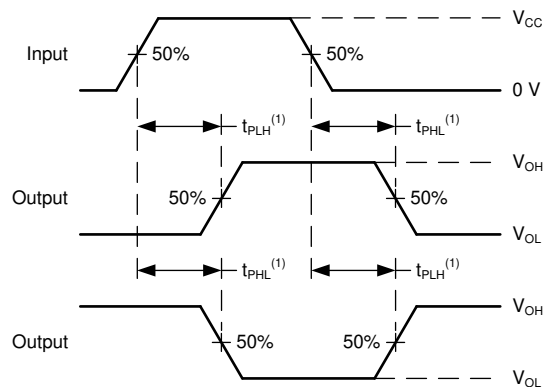
For clock inputs, f_{max} is measured when the input duty cycle is 50%.

The outputs are measured one at a time with one input transition per measurement.



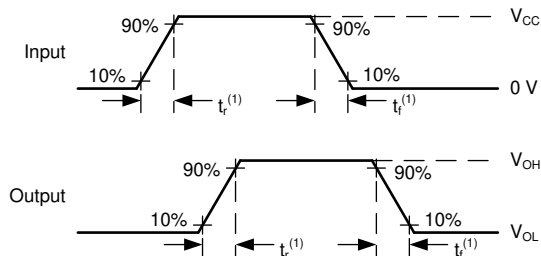
(1) C_L includes probe and test-fixture capacitance.

Figure 7-1. Load Circuit for Push-Pull Outputs



(1) The greater between t_{PLH} and t_{PHL} is the same as t_{pd} .

Figure 7-2. Voltage Waveforms Propagation Delays



(1) The greater between t_r and t_f is the same as t_t .

Figure 7-3. Voltage Waveforms, Input and Output Transition Times

8 Detailed Description

8.1 Overview

This device contains four independent 2-input NAND gates with Schmitt-trigger inputs. Each gate performs the Boolean function $Y = \overline{A \bullet B}$ in positive logic.

8.2 Functional Block Diagram

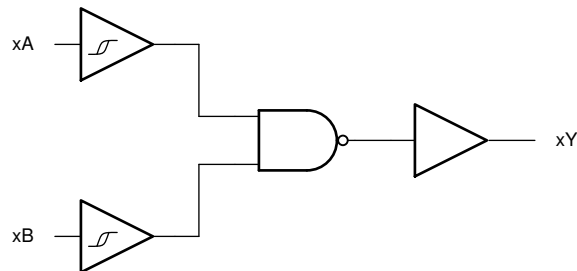


Figure 8-1. Logic Diagram (Positive Logic) for the SN74HC132

8.3 Balanced CMOS Push-Pull Outputs

This device includes balanced CMOS push-pull outputs. The term "balanced" indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

Unused push-pull CMOS outputs should be left disconnected.

8.4 CMOS Schmitt-Trigger Inputs

This device includes inputs with the Schmitt-trigger architecture. These inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics* table from the input to ground. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings* table, and the maximum input leakage current, given in the *Electrical Characteristics* table, using Ohm's law ($R = V \div I$).

The Schmitt-trigger input architecture provides hysteresis as defined by ΔV_T in the *Electrical Characteristics* table, which makes this device extremely tolerant to slow or noisy inputs. While the inputs can be driven much slower than standard CMOS inputs, it is still recommended to properly terminate unused inputs. Driving the inputs with slow transitioning signals will increase dynamic current consumption of the device. For additional information regarding Schmitt-trigger inputs, please see [Understanding Schmitt Triggers](#).

8.5 Clamp Diode Structure

The inputs and outputs to this device have both positive and negative clamping diodes as depicted in [Electrical Placement of Clamping Diodes for Each Input and Output](#).

CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

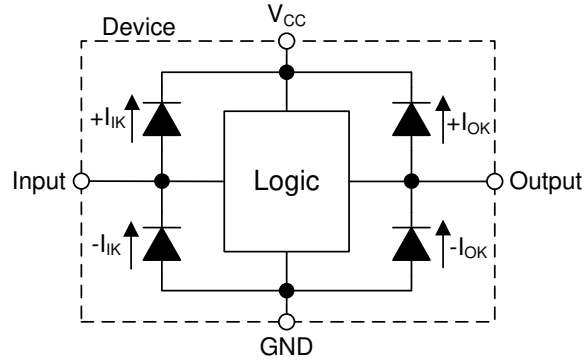


Figure 8-2. Electrical Placement of Clamping Diodes for Each Input and Output

8.6 Device Functional Modes

Table 8-1. Function Table

INPUTS		OUTPUT
A	B	Y
H	H	L
L	X	H
X	L	H

9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

In this application, the SN74HC132 is used to create an active-low SR latch. The two additional gates can be used for a second active-low SR latch, individually used for their logic function, or the inputs can be grounded and both channels left unused. This device is used to drive the tamper indicator LED and provide one bit of data to the system controller. When the tamper switch outputs LOW, the output Q becomes HIGH. This output remains HIGH until the system controller addresses the event and sends a LOW signal to the R input which returns the Q output back to LOW.

9.2 Typical Application

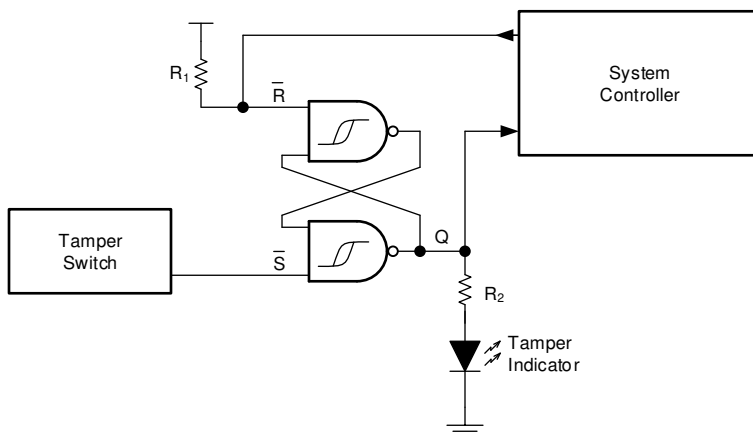


Figure 9-1. Typical application diagram

9.2.1 Design Requirements

9.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics as described in the *Electrical Characteristics*.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74HC132 plus the maximum static supply current, I_{CC} , listed in *Electrical Characteristics* and any transient current required for switching. The logic device can only source as much current as is provided by the positive supply source. Be sure not to exceed the maximum total current through V_{CC} listed in the *Absolute Maximum Ratings*.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74HC132 plus the maximum supply current, I_{CC} , listed in *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current as can be sunk into its ground connection. Be sure not to exceed the maximum total current through GND listed in the *Absolute Maximum Ratings*.

The SN74HC132 can drive a load with a total capacitance less than or equal to 50 pF while still meeting all of the datasheet specifications. Larger capacitive loads can be applied, however it is not recommended to exceed 50 pF.

The SN74HC132 can drive a load with total resistance described by $R_L \geq V_O / I_O$, with the output voltage and current defined in the *Electrical Characteristics* table with V_{OH} and V_{OL} . When outputting in the high state, the

output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Total power consumption can be calculated using the information provided in [CMOS Power Consumption and Cpd Calculation](#).

Thermal increase can be calculated using the information provided in [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices](#).

CAUTION

The maximum junction temperature, $T_{J(max)}$ listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

9.2.1.2 Input Considerations

Input signals must cross $V_{t-(min)}$ to be considered a logic LOW, and $V_{t+(max)}$ to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either V_{CC} or ground. These can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input is to be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The resistor size is limited by drive current of the controller, leakage current into the SN74HC132, as specified in the *Electrical Characteristics*, and the desired input transition rate. A 10-k Ω resistor value is often used due to these factors.

The SN74HC132 has no input signal transition rate requirements because it has Schmitt-trigger inputs.

Another benefit to having Schmitt-trigger inputs is the ability to reject noise. Noise with a large enough amplitude can still cause issues. To know how much noise is too much, please refer to the $\Delta V_{T(min)}$ in the *Electrical Characteristics*. This hysteresis value will provide the peak-to-peak limit.

Unlike what happens with standard CMOS inputs, Schmitt-trigger inputs can be held at any valid value without causing huge increases in power consumption. The typical additional current caused by holding an input at a value other than V_{CC} or ground is plotted in the *Typical Characteristics*.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

9.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the V_{OH} specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to *Feature Description* section for additional information regarding the outputs for this device.

9.2.2 Detailed Design Procedure

1. Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the *Layout* section.

2. Ensure the capacitive load at the output is ≤ 50 pF. This is not a hard limit, however it will ensure optimal performance. This can be accomplished by providing short, appropriately sized traces from the SN74HC132 to the receiving device(s).
3. Ensure the resistive load at the output is larger than $(V_{CC} / I_{O(max)}) \Omega$. This will ensure that the maximum output current from the *Absolute Maximum Ratings* is not violated. Most CMOS inputs have a resistive load measured in megaohms; much larger than the minimum calculated above.
4. Thermal issues are rarely a concern for logic gates, however the power consumption and thermal increase can be calculated using the steps provided in the application report, [CMOS Power Consumption and Cpd Calculation](#).

9.2.3 Application Curve

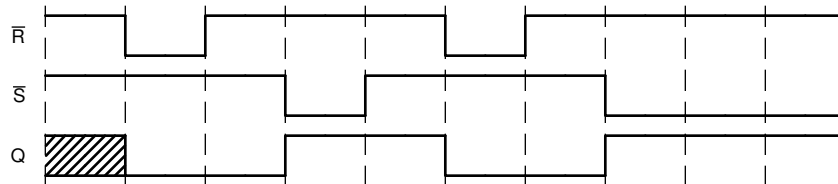


Figure 9-2. Application timing diagram

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A 0.1- μF capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1- μF and 1- μF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in given example layout image.

11 Layout

11.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC} , whichever makes more sense for the logic function or is more convenient.

11.2 Layout Example

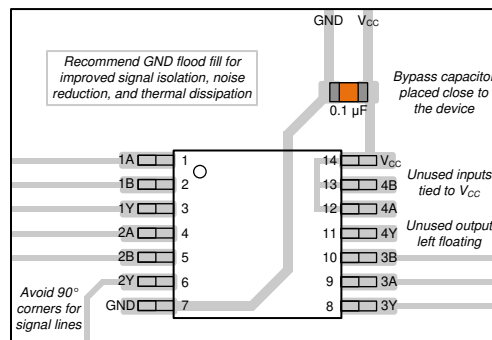


Figure 11-1. Example layout for the SN74HC132.

12 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

12.1 Documentation Support

12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.3 Support Resources

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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12.4 Trademarks

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12.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.6 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
5962-89845022A	ACTIVE	LCCC	FK	20	55	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-89845022A SNJ54HC 132FK	Samples
5962-8984502CA	ACTIVE	CDIP	J	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-8984502CA SNJ54HC132J	Samples
5962-8984502DA	ACTIVE	CFP	W	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-8984502DA SNJ54HC132W	Samples
5962-8984502VCA	ACTIVE	CDIP	J	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-8984502VC A SNV54HC132J	Samples
5962-8984502VDA	ACTIVE	CFP	W	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-8984502VD A SNV54HC132W	Samples
SN54HC132J	ACTIVE	CDIP	J	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	SN54HC132J	Samples
SN74HC132D	OBSOLETE	SOIC	D	14		TBD	Call TI	Call TI	-40 to 85	HC132	
SN74HC132DBR	ACTIVE	SSOP	DB	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC132	Samples
SN74HC132DR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	HC132	Samples
SN74HC132DT	OBSOLETE	SOIC	D	14		TBD	Call TI	Call TI	-40 to 85	HC132	
SN74HC132N	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 85	SN74HC132N	Samples
SN74HC132NE4	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 85	SN74HC132N	Samples
SN74HC132NSR	ACTIVE	SO	NS	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC132	Samples
SN74HC132NSRG4	ACTIVE	SO	NS	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC132	Samples
SN74HC132PW	OBSOLETE	TSSOP	PW	14		TBD	Call TI	Call TI	-40 to 85	HC132	
SN74HC132PWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	HC132	Samples
SN74HC132PWT	OBSOLETE	TSSOP	PW	14		TBD	Call TI	Call TI	-40 to 85	HC132	
SNJ54HC132FK	ACTIVE	LCCC	FK	20	55	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-89845022A	Samples

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
										SNJ54HC 132FK	
SNJ54HC132J	ACTIVE	CDIP	J	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-8984502CA SNJ54HC132J	Samples
SNJ54HC132W	ACTIVE	CFP	W	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-8984502DA SNJ54HC132W	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBsolete: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF SN54HC132, SN54HC132-SP, SN74HC132 :

- Catalog : [SN74HC132](#), [SN54HC132](#)
- Automotive : [SN74HC132-Q1](#), [SN74HC132-Q1](#)
- Military : [SN54HC132](#)
- Space : [SN54HC132-SP](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product
- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects
- Military - QML certified for Military and Defense Applications
- Space - Radiation tolerant, ceramic packaging and qualified for use in Space-based application

TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74HC132DBR	SSOP	DB	14	2000	330.0	16.4	8.35	6.6	2.4	12.0	16.0	Q1
SN74HC132DR	SOIC	D	14	2500	330.0	16.4	6.6	9.3	2.1	8.0	16.0	Q1
SN74HC132NSR	SO	NS	14	2000	330.0	16.4	8.45	10.55	2.5	12.0	16.2	Q1
SN74HC132PWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74HC132DBR	SSOP	DB	14	2000	356.0	356.0	35.0
SN74HC132DR	SOIC	D	14	2500	366.0	364.0	50.0
SN74HC132NSR	SO	NS	14	2000	356.0	356.0	35.0
SN74HC132PWR	TSSOP	PW	14	2000	356.0	356.0	35.0

TUBE


*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
5962-89845022A	FK	LCCC	20	55	506.98	12.06	2030	NA
5962-8984502DA	W	CFP	14	25	506.98	26.16	6220	NA
5962-8984502VDA	W	CFP	14	25	506.98	26.16	6220	NA
SN74HC132N	N	PDIP	14	25	506	13.97	11230	4.32
SN74HC132N	N	PDIP	14	25	506	13.97	11230	4.32
SN74HC132NE4	N	PDIP	14	25	506	13.97	11230	4.32
SN74HC132NE4	N	PDIP	14	25	506	13.97	11230	4.32
SNJ54HC132FK	FK	LCCC	20	55	506.98	12.06	2030	NA
SNJ54HC132W	W	CFP	14	25	506.98	26.16	6220	NA

W (R-GDFP-F14)

CERAMIC DUAL FLATPACK



4040180-2/F 04/14

- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - C. This package can be hermetically sealed with a ceramic lid using glass frit.
 - D. Index point is provided on cap for terminal identification only.
 - E. Falls within MIL STD 1835 GDFP1-F14

DB0014A



PACKAGE OUTLINE

SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. Reference JEDEC registration MO-150.

EXAMPLE BOARD LAYOUT

DB0014A

SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



4220762/A 05/2024

NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DB0014A

SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220762/A 05/2024

NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

GENERIC PACKAGE VIEW

FK 20

LCCC - 2.03 mm max height

8.89 x 8.89, 1.27 mm pitch

LEADLESS CERAMIC CHIP CARRIER

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



4229370VA\

J 14

GENERIC PACKAGE VIEW
CDIP - 5.08 mm max height
CERAMIC DUAL IN LINE PACKAGE



Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

4040083-5/G

J0014A



PACKAGE OUTLINE

CDIP - 5.08 mm max height

CERAMIC DUAL IN LINE PACKAGE



NOTES:

1. All controlling linear dimensions are in inches. Dimensions in brackets are in millimeters. Any dimension in brackets or parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This package is hermetically sealed with a ceramic lid using glass frit.
4. Index point is provided on cap for terminal identification only and on press ceramic glass frit seal only.
5. Falls within MIL-STD-1835 and GDIP1-T14.

EXAMPLE BOARD LAYOUT

J0014A

CDIP - 5.08 mm max height

CERAMIC DUAL IN LINE PACKAGE



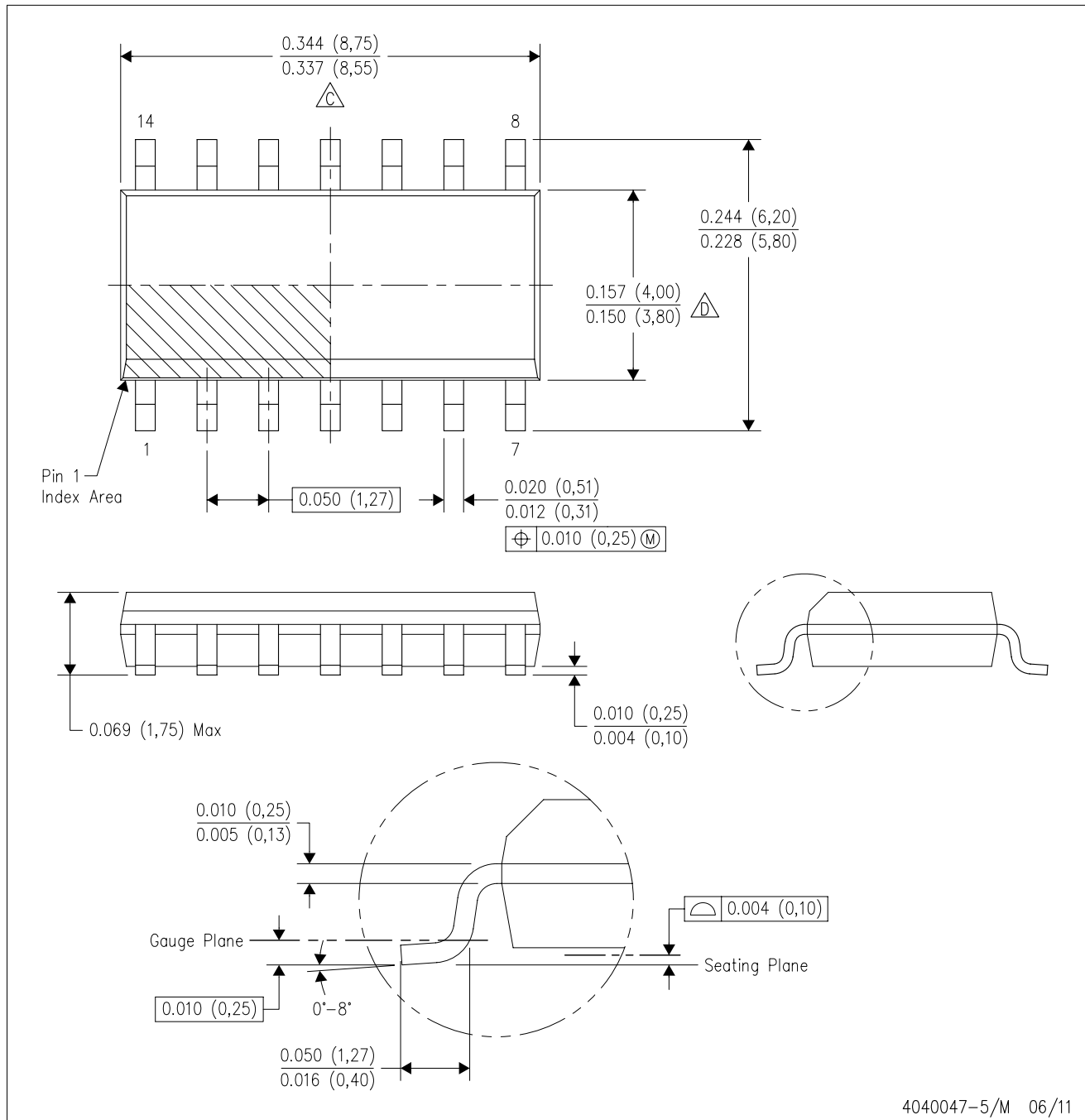
LAND PATTERN EXAMPLE
NON-SOLDER MASK DEFINED
SCALE: 5X



4214771/A 05/2017

D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 -  Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
 -  Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
 - E. Reference JEDEC MS-012 variation AB.

PW (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - B. This drawing is subject to change without notice.
 - C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
 - D. Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
 - E. Falls within JEDEC MO-153

N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
 - The 20 pin end lead shoulder width is a vendor option, either half or full width.

MECHANICAL DATA

NS (R-PDSO-G**)

PLASTIC SMALL-OUTLINE PACKAGE

14-PINS SHOWN



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.

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